

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1-24 (Canceled)

25. (Currently amended) An intermediate semiconductor component, comprising:
a substrate having a first surface and an opposing, second surface and including an aperture that communicates with the first surface and extends partially through the substrate; and
at least one via extending into the first surface of the substrate and terminating short of the opposing, second surface; ~~wherein the at least one via comprises~~ and including a seed layer at least partially over a surface of the aperture, an annular conductive layer that extends from the first surface contacting the seed layer, and circumscribes a filler material circumscribed by and contacting the annular conductive layer.

26. (Currently amended) The intermediate semiconductor component of claim 25,
wherein the annular conductive layer comprises a metal layer formed on a the seed layer, ~~wherein the seed layer is located between the metal layer and the substrate.~~

27. (Original) The intermediate semiconductor component of claim 25, wherein the filler material is selected from the group consisting of spin-on-glass, polysilicon, solder paste and a solder alloy.

28. (Original) The intermediate semiconductor component of claim 25, wherein the filler material is either a conductive or a nonconductive filler material.

29. (Previously Presented) The intermediate semiconductor component of claim 26, wherein the seed layer is selected from the group consisting of titanium nitride, titanium, tantalum nitride, copper, silicon nitride, and a polysilicon.

30. (Original) The intermediate semiconductor component of claim 26, wherein the metal layer is selected from the group of metals consisting of nickel, cobalt, copper, silver, titanium, iridium, gold, tungsten, tantalum, molybdenum, platinum, palladium, nickel-phosphorus, palladium-phosphorus, cobalt-phosphorus, a Co-W-P alloy, alloys of the foregoing metals and mixtures of any of the foregoing.

31. (Original) The intermediate semiconductor component of claim 25, further comprising an insulative layer located between the annular conductive layer and the substrate.

32. (Original) The intermediate semiconductor component of claim 25, further comprising a barrier layer on the first surface.

33-63 (Canceled)

64. (Currently amended) An intermediate semiconductor component, comprising: a substrate having a first surface and an opposing, second surface; and at least one via extending into the first surface of the substrate and terminating short of the opposing, second surface and including ~~wherein the at least one via includes conductive filler material comprising a solder alloy that extends from the first surface.~~

65. (Previously Presented) The intermediate semiconductor component of claim 64, further comprising an insulative layer located between the conductive filler material and the substrate.

66. (Previously Presented) The intermediate semiconductor component of claim 64, further comprising a barrier layer on the first surface.

67-72 (Canceled)